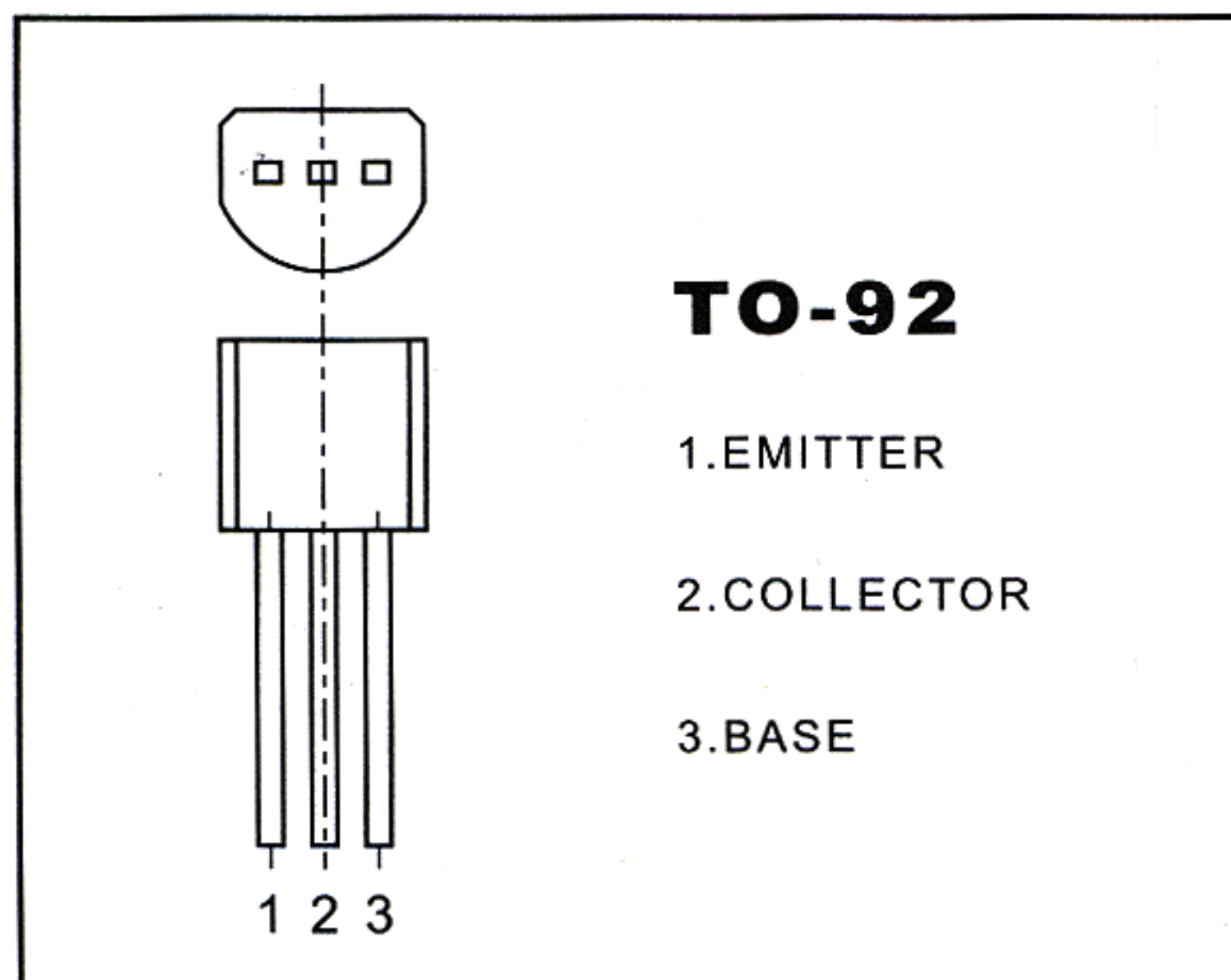


KTC3194 TRANSISTOR(NPN)



FEATURES

Power dissipation

P_{CM} : 0.625W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 0.02 A

Collector-base voltage

$V_{(BR)CBO}$: 40 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100 \mu A, I_E = 0$	40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1 mA, I_B = 0$	30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100 \mu A, I_C = 0$	4		V
Collector cut-off current	I_{CBO}	$V_{CB} = 40 V, I_E = 0$		0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 4 V, I_C = 0$		0.5	μA
DC current gain	h_{FE}	$V_{CE} = 6 V, I_C = 1 mA$	40	200	
Transition frequency	f_T	$V_{CE} = 6 V, I_C = 1 mA$	450		MHz

CLASSIFICATION OF h_{FE}

Rank	R	O	Y
Range	40-80	70-140	100-200